

**IN THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (currently amended): A substrate treatment process for removing organic matter existing on a substrate, comprising treating said substrate with ozone water prepared by dissolving an ozone-containing gas in ultrapure water and hydrogen water prepared by dissolving a hydrogen-containing gas in ultrapure water in tandem, wherein said ozone water includes at least one substance selected from the group consisting of carbon dioxide, ammonium carbonate, acetic acid, and formic acid in an amount sufficient to maintain an ozone concentration of said ozone water.

Claim 2 (withdrawn): A substrate treatment process for removing organic matter existing on a substrate, which comprises the following step:

treating said substrate with ozone-hydrogen water, which has been prepared by dissolving an ozone-containing gas and a hydrogen-containing gas in ultrapure water, or with ozone hydrogen water prepared by mixing ozone water, which was in turn prepared by dissolving an ozone-containing gas in ultrapure water, and hydrogen water which was in turn prepared by dissolving a hydrogen-containing gas in ultrapure water; or treating said substrate with said ozone water and said hydrogen water at the same time.

Claim 3 (previously presented): A substrate treatment process according to claim 1 or 2, wherein said substrate to be treated is one of a glass substrate and a substrate comprising one of silicon crystal and metal compound crystal.

Claim 4 (original): A substrate treatment process according to claim 1 or 2, wherein said substrate to be treated is a substrate contaminated with organic matter or ion-implanted organic matter.

Claim 5 (original): A substrate treatment process according to claim 1 or 2, wherein said substrate to be treated is a substrate contaminated with organic matter adhered in a semiconductor element fabrication process.

Claim 6 (currently amended): A substrate treatment process according to claim 1 [[or 2]], wherein said ~~ozone water has an~~ ozone concentration is not lower than 10 ppm.

Claim 7 (original): A substrate treatment process according to claim 1 or 2, wherein said hydrogen water has a hydrogen concentration not lower than 0.5 ppm.

Claim 8 (previously presented): A substrate treatment process according to claim 1, wherein said ozone water is applied to said substrate under treatment at a rate not lower than 1 mL/min per square centimeter of substrate area.

Claim 9 (previously presented): A substrate treatment process according to claim 1, wherein said hydrogen water is applied to said substrate under treatment after activating said hydrogen water by ultrasonic treatment.

Claim 10 (original): A substrate treatment process according to claim 1 or 2, wherein said substrate is treated under rotation in a horizontal plane.

Claim 11 (original): A substrate treatment process according to claim 10, wherein said substrate is rotated at a rotational speed not lower than 500 rpm.

Claim 12 (original): A substrate treatment process according to claim 1 or 2, wherein said substrate is treated in the same treatment apparatus.

Claim 13 (original): A substrate treatment process according to claim 1 or 2, wherein said substrate is treated while being heated at a temperature not lower than 30° C.

Claim 14 (original): A substrate treatment process according to claim 13, wherein said heating is performed while introducing heated ultrapure water or heated nitrogen.

Claim 15 (previously presented): A substrate treatment process according to claim 1, wherein said organic matter is subjected to ashing with an oxidizing gas before the step in which the substrate is treated with one of said ozone water and said hydrogen water.

Claim 16 (original): A substrate treatment process according to claim 15, wherein said oxidizing gas is an ozone-containing gas; and said substrate is subjected to ashing at least once in a dry atmosphere while being heated at a temperature not lower than room temperature.

Claim 17 (original): A substrate treatment process according to claim 16, wherein said substrate under ashing is heated at 300 to 350° C.

Claim 18 (original): A substrate treatment process according to claim 17, wherein said ozone- containing gas has an ozone concentration not lower than 4 vol.%.

Claim 19 (previously presented): A substrate treatment process according to claim 1, wherein said substrate is cleaned with an organic solvent before the step in which the substrate is treated with one of said ozone water and said hydrogen water.

Claim 20 (previously presented): A substrate treatment process according to claim 1, wherein said substrate is treated with HF-containing water after the step in which the substrate is treated with one of said ozone water and said hydrogen water.

Claim 21 (withdrawn): A substrate treatment apparatus for a substrate, comprising:  
a treatment vessel,  
a substrate holder for rotating said substrate in a horizontal plane in said treatment vessel,  
a nozzle unit arranged in an upper part of said treatment vessel such that a liquid is downwardly fed,  
a feed line for feeding the liquid to said nozzle unit,

and

a chamber enclosing therein said apparatus in its entirety;

wherein said nozzle unit is constructed in a form of a bar such that as viewed in plan, the liquid ejected from said nozzle unit reaches, with an area range having a length not smaller than a diameter of said substrate and a width smaller than said diameter of said substrate, said substrate.

Claim 22 (withdrawn): A substrate treatment apparatus according to claim 21, further comprising an ultrasonic wave generator arranged in said nozzle unit.

Claim 23 (withdrawn): A substrate treatment apparatus according to claim 22, wherein said nozzle unit is provided with at least one flow channel for ozone water, at least one flow channel for hydrogen water or at least one flow channel for ozone-hydrogen water; and said flow channel is shielded from ultrasonic waves.